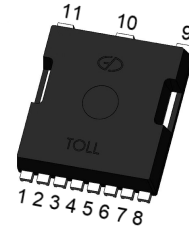


## N-Channel 100V (D-S) Power MOSFET

### Features

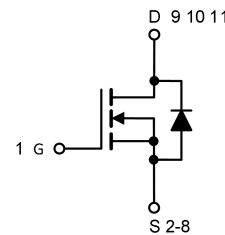
- 100% Avalanche Tested
- Extremely Low Losses with Low FOM  $R_{ds(on)} \cdot Q_g$
- RoHS Compliant, Halogen Free, Pb-Free
- AEC-Q101 Qualified
- MSL 1



TOLL

### Applications

- Automotive systems
- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit



### Absolute Maximum Ratings ( $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain Source Voltage	$V_{DS}$	100	V
Gate Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current, Continuous $V_{GS}=10\text{V}$ (Note 1)	$I_D$	$T_C=25^\circ\text{C}$	224
		$T_C=100^\circ\text{C}$	141
Drain Current, Pulsed (Note 2)	$I_{DM}$	896	A
Single Avalanche Energy	$E_{AS}$	795	mJ
Power Dissipation (Note 3)	$P_D$	208	W
Operating Junction/ Storage Temperature Range	$T_J/ T_{STG}$	-55 to +150	$^\circ\text{C}$

Note 1: Calculated continuous current based on maximum allowable junction temperature.

Note 2: Repetitive rating; pulse width limited by max. junction temperature.

### Thermal Characteristics

Parameter	Symbol	Max	Unit
Junction to Case (Note 3)	$R_{\theta JC}$	0.6	$^\circ\text{C/W}$
Junction-to-ambient ( $t \leq 10\text{s}$ )(Note 4)	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Note 3: The power dissipation  $P_D$  is based on max. junction temperature, using junction-to-case thermal resistance.

Note 4: The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$

### Electrical Characteristics (T<sub>J</sub> =25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	--	--	1	uA
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	--	4	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V	--	--	±100	nA
Drain-Source On-state Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =50A	--	1.8	3	mΩ
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =100A	--	106	--	nC
Gate Source Charge	Q <sub>gs</sub>		--	41	--	
Gate Drain Charge	Q <sub>gd</sub>		--	30	--	
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V, R <sub>L</sub> =1Ω, R <sub>GEN</sub> =2.2Ω	--	39	--	ns
Turn-on Rise Time	t <sub>r</sub>		--	15	--	
Turn-off Delay Time	t <sub>d(off)</sub>		--	50	--	
Turn-off Fall Time	t <sub>f</sub>		--	16	--	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =50V, f=100kHz	--	6209	--	pF
Output Capacitance	C <sub>oss</sub>		--	2570	--	
Reverse Transfer Capacitance	C <sub>rss</sub>		--	67	--	

### Reverse Diode Characteristics (T<sub>J</sub> =25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Current, Continuous	I <sub>S</sub>	T <sub>C</sub> =25°C	--	--	224	A
Pulsed Source Current (Body Diode)	I <sub>SM</sub>		--	--	896	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =50A, V <sub>GS</sub> =0V	--	--	1.2	V
Reverse Recovery Time	T <sub>rr</sub>	V <sub>R</sub> =50V, I <sub>F</sub> =50A, di/dt = 100 A/μs	--	75	--	ns
Reverse Recovery Charge	Q <sub>rr</sub>		--	123	--	nC

## Typical Characteristics Curves ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Fig.1 - Typical Output Characteristics

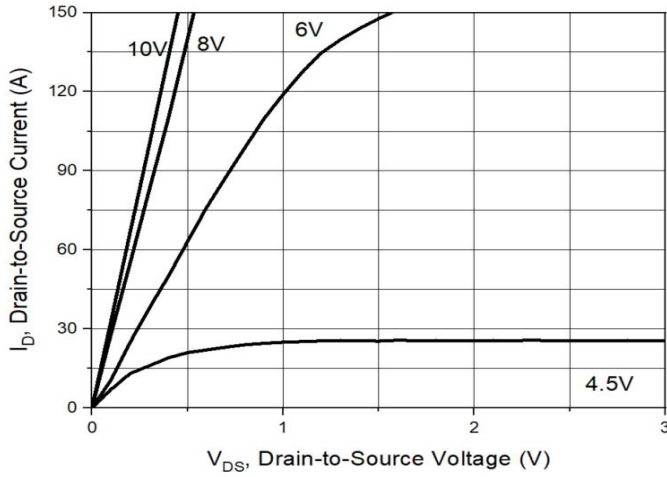


Fig.2 - Drain-to-Source Breakdown Voltage vs. Junction Temperature

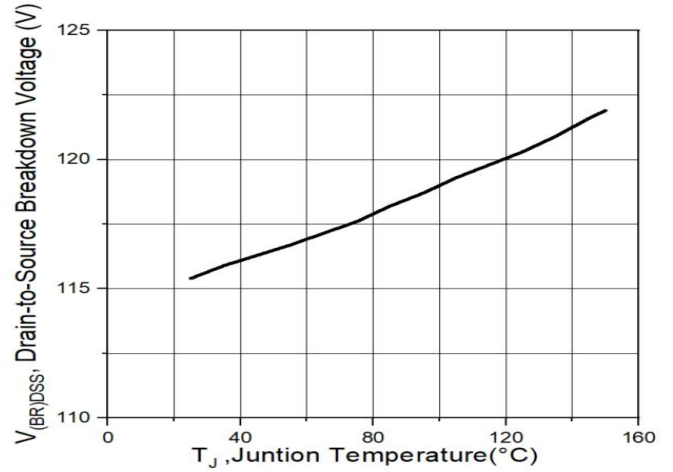


Fig.3 -  $R_{DS(on)}$  vs. Junction Temperature

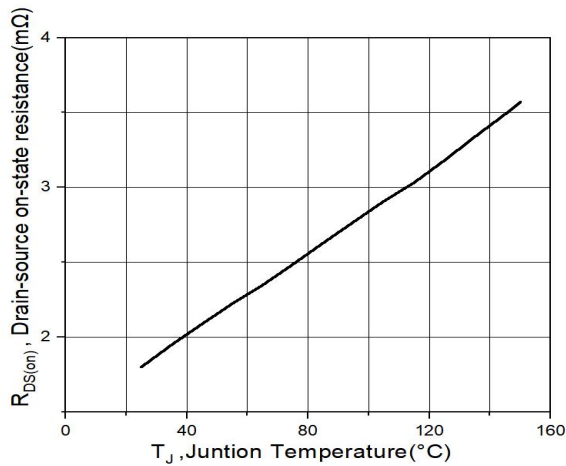


Fig.4 -  $V_{th}$  vs. Junction Temperature

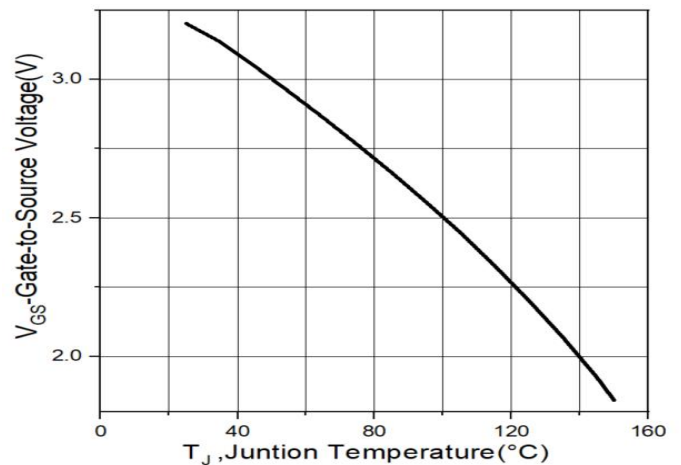


Fig.5 - Capacitance

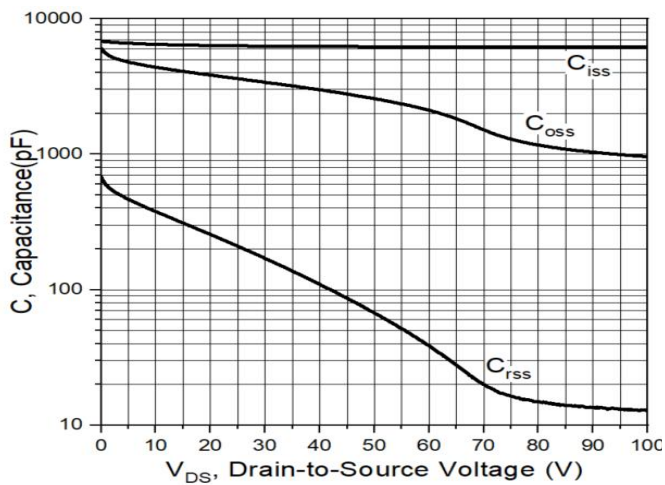
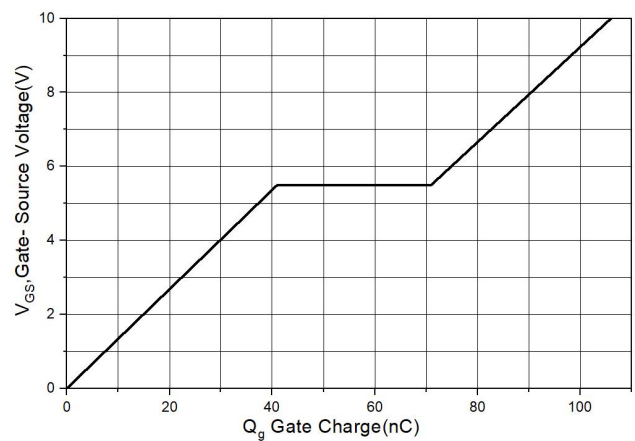


Fig.6 - Gate Charge



**Typical Characteristics Curves** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Fig.7 - Transfer Characteristics

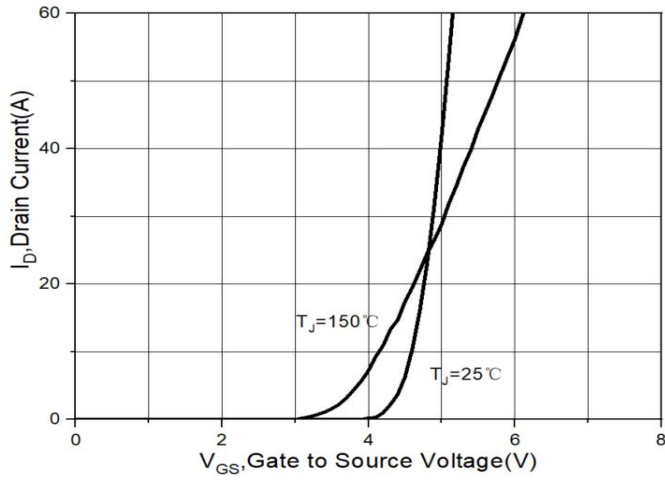
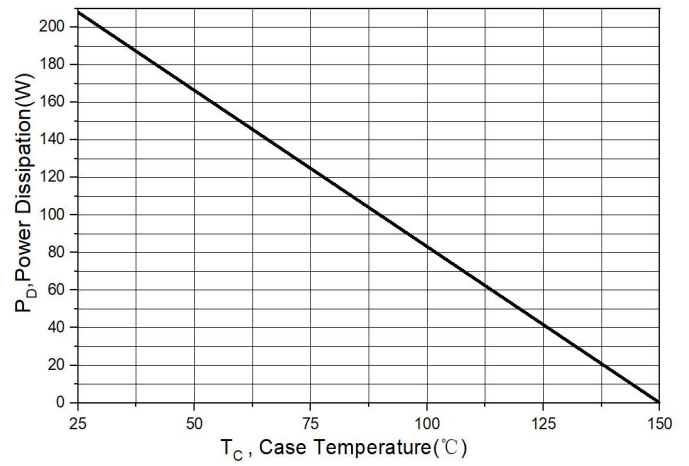
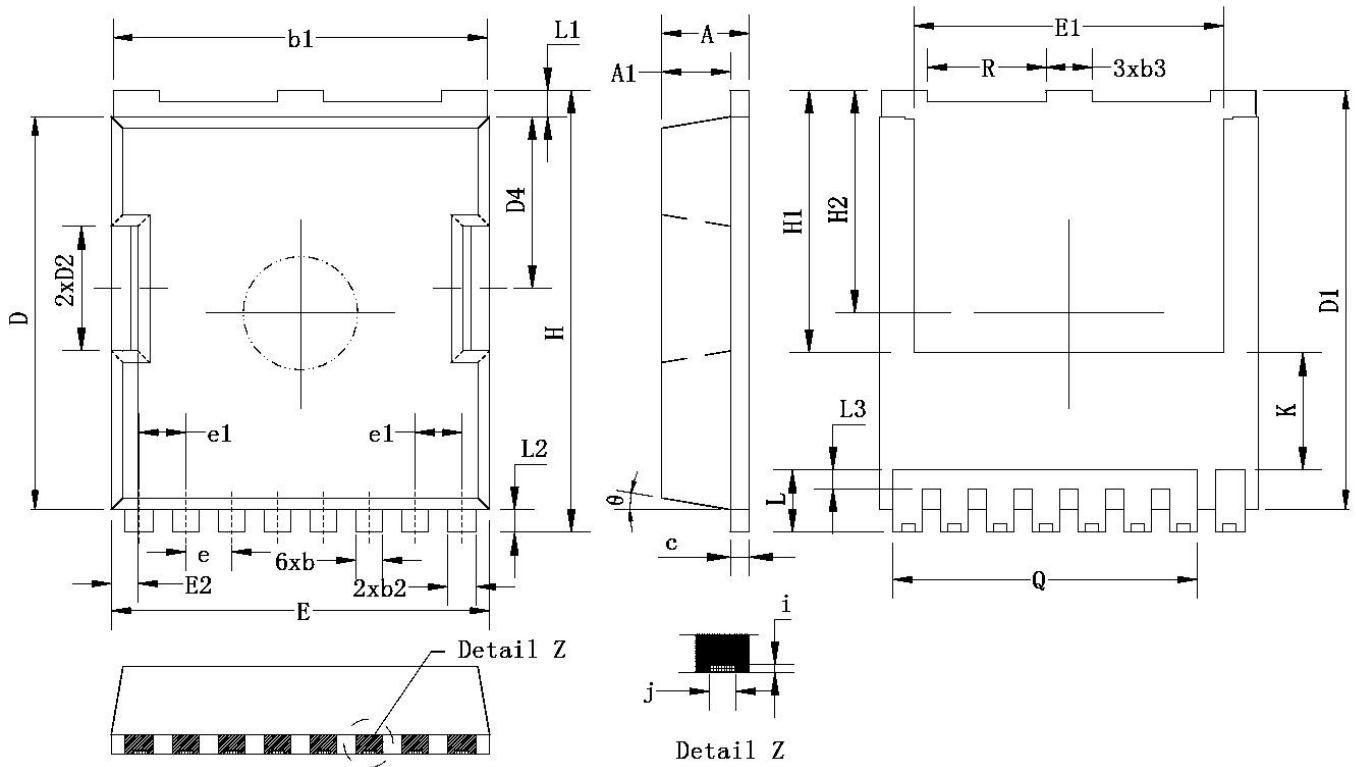


Fig.8 - Power Dissipation



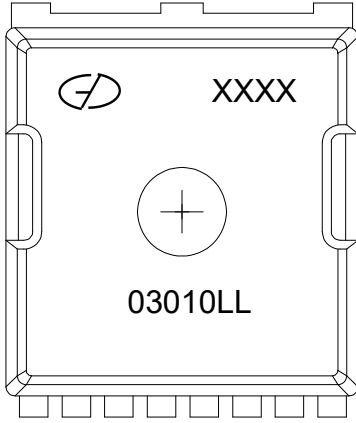
## Package Outline Dimensions (Unit: millimeters)

### TOLL




Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	2.25	2.30	2.35	E2	0.65	0.70	0.75
A1	1.75	1.80	1.85	H	11.60	11.70	11.80
b	0.65	0.70	0.75	H1	6.95 BSC		
b1	9.75	9.80	9.85	H2	5.90 BSC		
b2	0.70	0.75	0.80	i	0.10 REF		
b3	1.15	1.20	1.25	j	0.35 REF		
c	0.45	0.50	0.55	K	3.10 REF		
D	10.35	10.40	10.45	L	1.55	1.65	1.75
D1	11.00	11.10	11.20	L1	0.65	0.70	0.75
D2	3.25	3.30	3.35	L2	0.50	0.60	0.70
D4	4.50	4.55	4.60	L3	0.40	0.50	0.60
e	1.20 BSC			Q	7.95 REF		
e1	1.225 BSC			R	3.05	3.10	3.15
E	9.85	9.90	9.95	θ	10°REF		
E1	8.00	8.10	8.20				

## Marking Outline



Part Name: GMN03010LL

1. Logo Mark: 
2. Date Code: XXXX
3. P/N Mark: 03010LL

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